後段金屬原子層奈米孔洞沉積系統

Deposition Process Library

- Titanium nitride (TiN)

Thickness

- 20A ~ 200Å

Process parameters

- Process: NH_3
- Precursor: TiCl4
- Pressure(torr): 0.5~1.5
- Carrier gas: Ar
- Purge gas: Ar
- Temperature (℃): 400 ℃
- Substrate size: 6, 8 inch, chip